

Supplementary material

Tuning the Dielectric and Microwaves Absorption Properties of N-Doped Carbon Nanotubes by Boron Insertion

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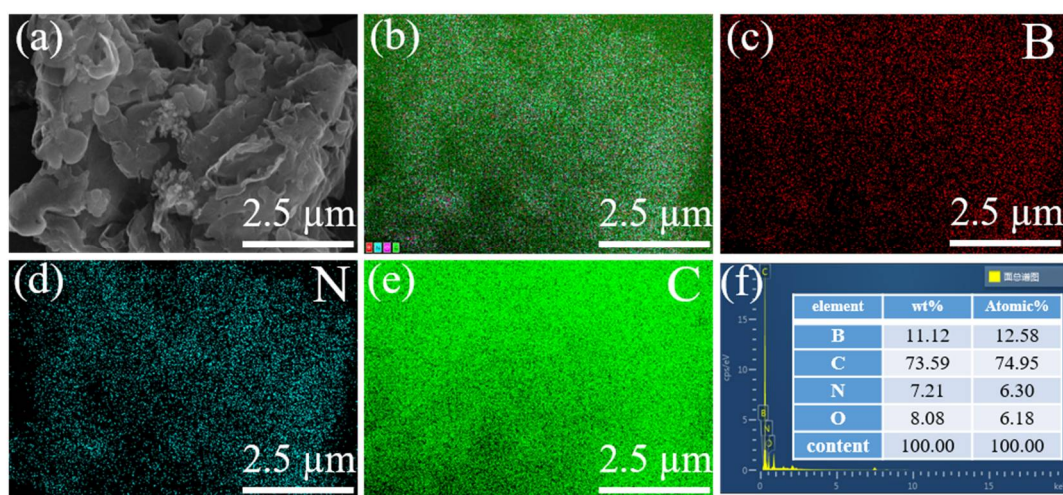


Figure S1. Element mapping analysis of B,N-CNT-5: SEM image (a), overall element distribution (b), B element (c), N element (d), C element (e) and element content (f).

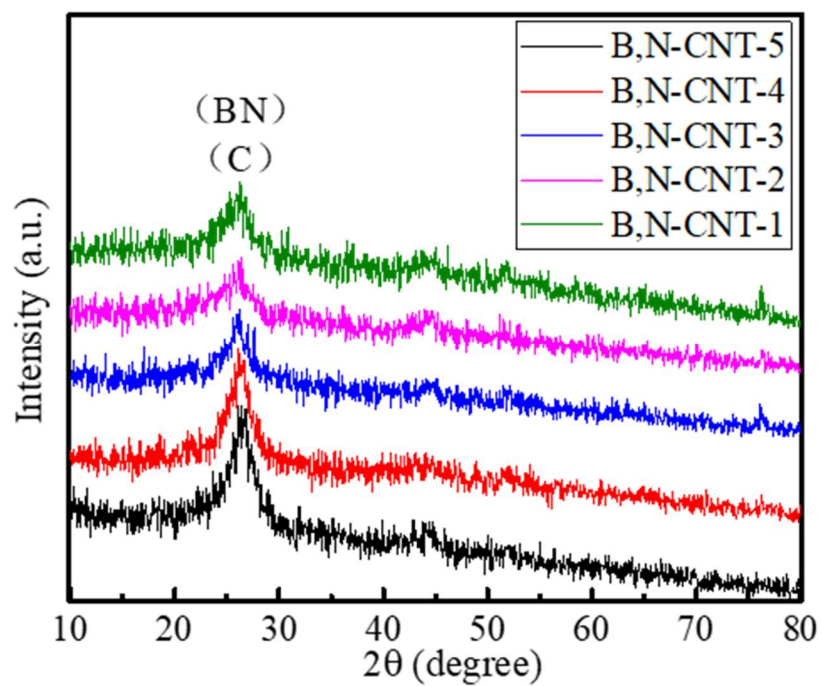


Figure S2. The XRD patterns of B,N-CNTs.

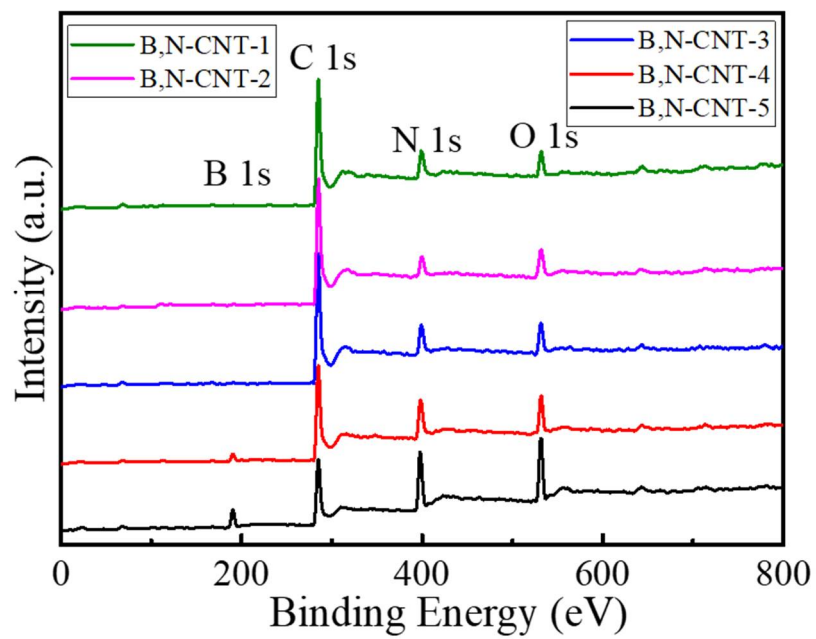


Figure S3. The survey spectrums of B,N-CNTs.

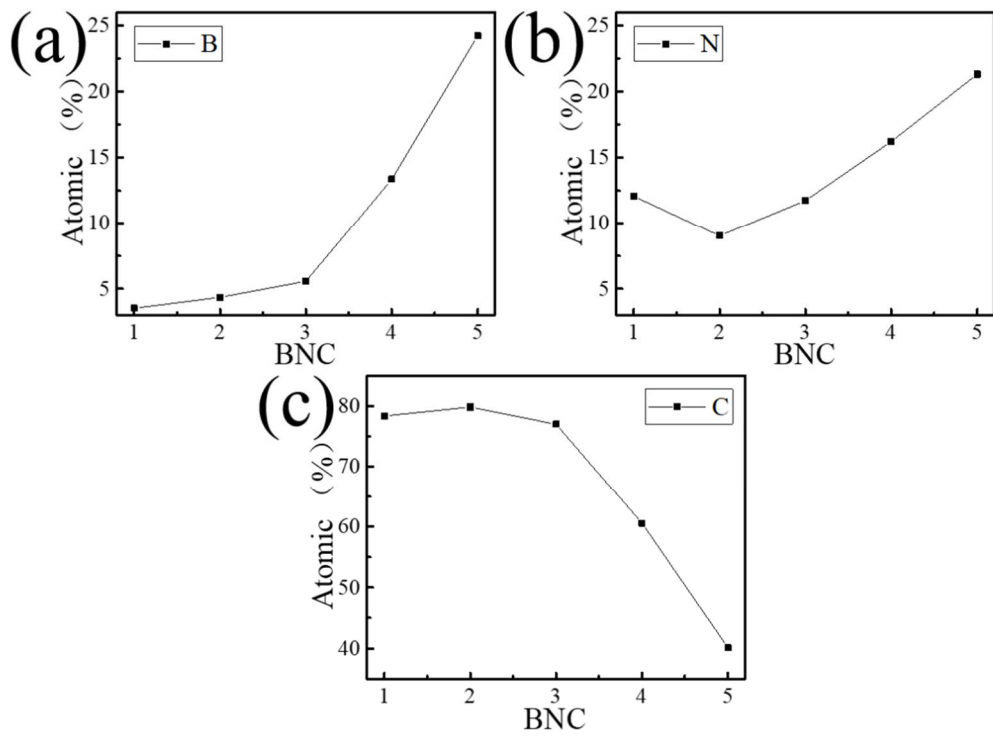


Figure S4. The atomic ratios of B (a), N (b) and C (c) in B,N-CNTs.

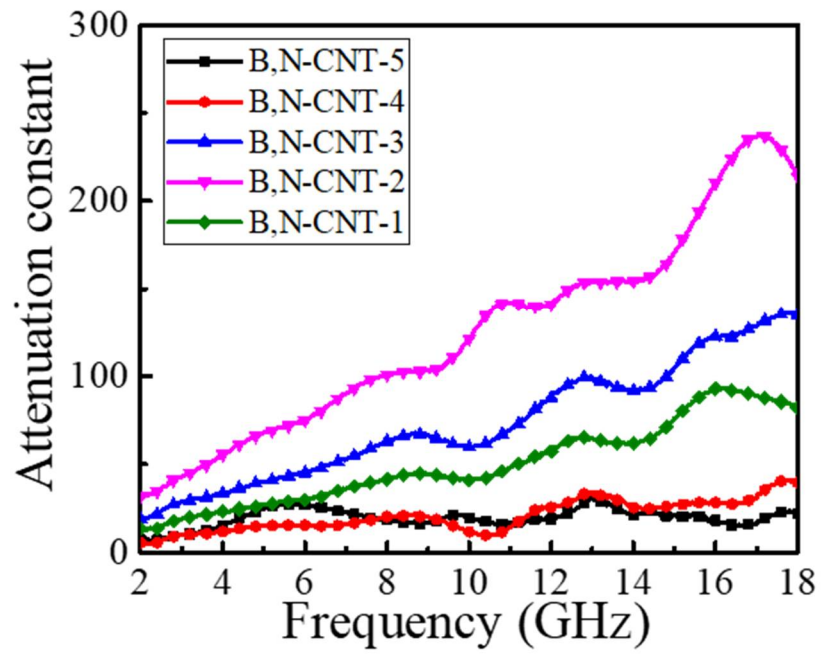


Figure S5. The Attenuation Constant curves of B,N-CNTs.

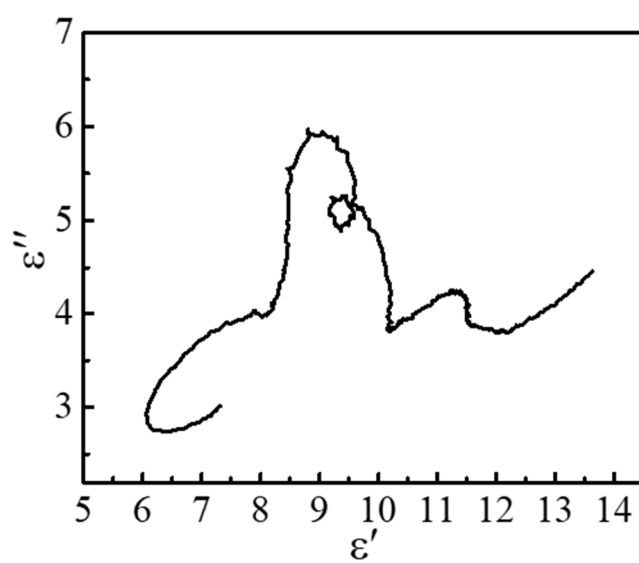


Figure S6. The Cole-Cole curve of B,N-CNT-2.